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Filing Date	10/17/2005	NOV 1 5 2005
First Named Inventor	Tadahiro OHMI	10
Group Art Unit	Unassigned	King of
Examiner Name	Unassigned	TRADE
Attorney Docket Number	039262-0143	

U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	U.S. Patent Document			Date of Publication of	Pages, Columns, Lines, Where Relevant	
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/T.T./	B1	wo	97/39476		MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD.	03-17-1995		A
								
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	NON PATENT LITERATURE DOCUMENTS	
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BZ	Wi. <u>SATOH</u> , et al., "Banid Oxidation of SiC Using Microwave-Discharged 02 Plasma at Low Temperatures (<300°C)," Jap. J. of Applied Physics, Part 2, Warch 1, 2002, Vol. 41:3A, pp. L233-L235.	25 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5
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